

MA3D760

Silicon epitaxial planar type (cathode common)

For switching power supply

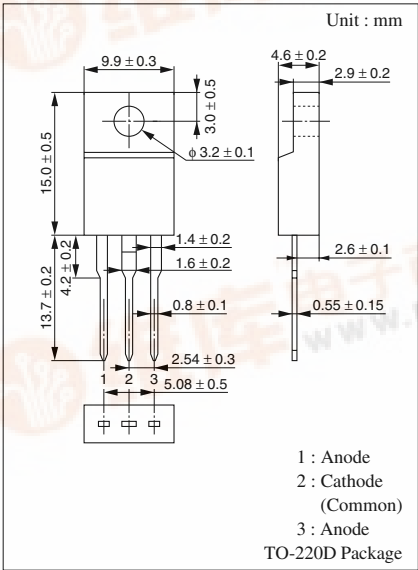
■ Features

- Low forward rise voltage V_F
- TO-220D (Full-pack package) with high dielectric breakdown voltage > 5.0 kV
- Easy-to-mount, caused by its V cut lead end

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	90	V
Average forward current	$I_{F(AV)}$	5	A
Non-repetitive peak forward surge current*	I_{FSM}	80	A
Junction temperature	T_j	-40 to $+125$	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to $+125$	$^\circ\text{C}$

Note) * : Half sine-wave; 10 ms/cycle



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 90$ V, $T_C = 25^\circ\text{C}$			1	mA
Forward voltage (DC)	V_F	$I_F = 2.5$ A, $T_C = 25^\circ\text{C}$			0.80	V
Thermal resistance*	$R_{th(j-c)}$	Direct current (between junction and case)			3	$^\circ\text{C/W}$

Note) 1. Rated input/output frequency: 200 MHz

2. * : $T_C = 25^\circ\text{C}$



